

a portion of said lower electrode layer is only embedded in said concave portion, and protrudes outward from an inner peripheral edge forming said concave portion, and a side of said portion of said lower electrode layer, a side of said ferroelectric layer and a side of said upper electrode layer are flush with each other.

2. (Twice Amended) A ferroelectric memory, comprising:

an insulation film having a hollow at a top surface; and

a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said hollow, wherein said laminated body includes a lower electrode layer, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer; and the memory further comprising another film embedded from said top surface of said insulation film in a position of a predetermined depth, exposed at a bottom of said hollow and separating between said insulation film and said lower electrode layer in said hollow, said another film being an etch stop for forming the hollow to said predetermined depth.